

L Number	Hits	Search Text	DB	Time stamp
1	73	"6140226"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 17:58
2	0	"6140226" and "Sioc-h"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 17:58
3	0	257/758 and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:01
4	2	257/\$.ccls. and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:01
5	3	438/\$.ccls. and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 17:59
6	0	361/\$.ccls. and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 17:59
7	0	29/\$.ccls. and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 17:59
8	0	174/\$.ccls. and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:00
9	3	(semiconductor or die or chip or IC) and "SiOC-H"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:00
10	69	(semiconductor or die or chip or IC) and "SiOCH"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:00
11	6	257/758 and "SiOCH"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:01
12	43	257/\$.ccls. and "SiOCH"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:04
13	48	438/\$.ccls. and "SiOCH"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 18:04
-	877	wafer and 257/48	USPAT	2004/06/14 01:20
-	1554	257/48	USPAT	2004/06/14 00:38
-	1	"4968931".PN.	USPAT	2004/06/14 01:01
-	1	"5504369".PN.	USPAT	2004/06/14 01:02
-	1	"5898186".PN.	USPAT	2004/06/14 01:02
-	1	"5962868".PN.	USPAT	2004/06/14 01:05

-	1	"6057171".PN.	USPAT	2004/06/14	01:05
-	1	"6175125".PN.	USPAT	2004/06/14	01:05
-	1	"6218848".PN.	USPAT	2004/06/14	01:05
-	1	"6281696".PN.	USPAT	2004/06/14	01:06
-	1	"6362638".PN.	USPAT	2004/06/14	01:06
-	1	"5292343".PN.	USPAT	2004/06/14	01:08
-	1	"5389556".PN.	USPAT	2004/06/14	01:09
-	1	"5391188".PN.	USPAT	2004/06/14	01:10
-	1	"5489538".PN.	USPAT	2004/06/14	01:10
-	1	"5532174".PN.	USPAT	2004/06/14	01:10
-	1	"5600257".PN.	USPAT	2004/06/14	01:11
-	1	"5532174".PN.	USPAT	2004/06/14	01:11
-	1	"5241266".PN.	USPAT	2004/06/14	01:17
-	1	"5254942".PN.	USPAT	2004/06/14	01:17
-	1	"5329471".PN.	USPAT	2004/06/14	01:18
-	1	"5396170".PN.	USPAT	2004/06/14	01:18
-	1	"5396170".PN.	USPAT	2004/06/14	01:18
-	1	"5408129".PN.	USPAT	2004/06/14	01:18
-	1	"5898186".PN.	USPAT	2004/06/14	01:18
-	1	"6233184".PN.	USPAT	2004/06/14	01:18
-	1	"6404660".PN.	USPAT	2004/06/14	01:19
-	1	"6411116".PN.	USPAT	2004/06/14	01:19
-	1	"6504359".PN.	USPAT	2004/06/14	01:20
-	47	"5389556"	USPAT	2004/06/14	01:24
-	33	"5532174"	USPAT	2004/06/14	02:22
-	9	"5327074"	USPAT	2004/06/14	02:56
-	613440	switch	USPAT	2004/06/14	02:56
-	40223	switch\$3 near transistor	USPAT	2004/06/14	02:56
-	28311	switch\$3 adj transistor	USPAT	2004/06/14	02:57
-	21862	switching adj transistor	USPAT	2004/06/14	03:13
-	25	(switching adj transistor) and 257/48	USPAT	2004/06/14	02:57
-	6	switching adj transistor with pad with (chip or dice or die)	USPAT	2004/06/14	03:14
-	1383	257/734	USPAT	2004/06/14	05:20
-	591	257/620	USPAT	2004/06/14	05:20
-	798	257/620	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:22
-	1917	257/691	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:24
-	540	257/665	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:26
-	2317	257/698	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:36
-	405	257/698	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:30
-	0	257/698 not 257/698	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:30
-	1912	257/698 not 257/698	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14	05:34

-	4	5494859.pn. or 6037664.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 05:35
-	3299	257/773	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 05:45
-	2690	257/773	USPAT	2004/06/14 05:37
-	609	257/773 not 257/773	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 05:39
-	849	257/735	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 05:49
-	678	257/741	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 05:51
-	2	5913147.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 05:50
-	2761	438/14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:03
-	396	438/14	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:01
-	2365	438/14 not 438/14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:03
-	863	438/462	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:13
-	221	barrier with (silicon near nitride or "Si" near "N") same (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 07:28
-	157	barrier with (silicon near nitride or "Si" near "N") same barrier with (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 07:44
-	5610	324/765	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:31
-	1805	324/765	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:14

-	3805	324/765 not 324/765	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:21
-	1753	324/765 not 324/765 and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:23
-	1264	324/763	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:41
-	1290	324/760	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:46
-	2	325/201	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 06:50
-	7	barrier near multi\$4 near (film or layer) same ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 07:27
-	10397	barrier near (films or layers) same ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 07:27
-	64	(barrier with (silicon near nitride or "Si" near "N") same (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper)) not (barrier with (silicon near nitride or "Si" near "N") same barrier with (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 07:28
-	78	barrier with (silicon near nitride or "Si" near "N") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:00
-	1	"5162258".PN.	USPAT	2004/06/14 07:58
-	1	"5812364".PN.	USPAT	2004/06/14 07:59
-	1	"5913126".PN.	USPAT	2004/06/14 07:59
-	1	"5918135".PN.	USPAT	2004/06/14 07:59
-	1	"5920775".PN.	USPAT	2004/06/14 07:59
-	78	barrier with (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:00
-	78	barrier with (silicon near nitride or "Si.sub.3N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:01
-	113	barrier same (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:16
-	446	barrier and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:16

-	59	barrier and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:25
-	93	(silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 11:17
-	34	((silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)) not (barrier and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 08:42
-	3066	silicon near nitride with dielectric near constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/14 09:29
-	1831	silicon near nitride with dielectric near constant	USPAT	2004/06/14 09:38
-	1	("FSO") with dielectric near constant	USPAT	2004/06/14 09:39
-	1	("FSO" or "fluonated silicon oxide") with dielectric near constant	USPAT	2004/06/14 09:39
-	1	("FSO" or fluonat\$3 near silicon near oxide) with dielectric near constant	USPAT	2004/06/14 09:45
-	1	(siliconoxynitride) with dielectric near constant	USPAT	2004/06/14 09:40
-	183	(bpsg) with dielectric near constant	USPAT	2004/06/14 10:07
-	1605	257/750	USPAT	2004/06/14 10:12
-	2141	257/751	USPAT	2004/06/14 10:21
-	987	257/752	USPAT	2004/06/14 10:22
-	3439	257/758	USPAT	2004/06/16 11:15
-	3	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 11:18
-	41	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") same (silicon near dioxide or "Si" near "O.sub.2") same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 11:24
-	358	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") same (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 11:24
-	553	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 15:13
-	2	"20030003765"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 12:45

-	2253	257/758 and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 13:16
-	1700	(257/758 and ("Cu" or copper)) not (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:16
-	382	257/751 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 15:56
-	182	257/752 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:07
-	791	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:08
-	802	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4" or "SiN") and (silicon near dioxide or "Si" near "O.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:08
-	590	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4" or "SiN") and (silicon near dioxide or "Si" near "O.sub.2" or "SiO") and ("Cu" or copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:09
-	37	(257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4" or "SiN") and (silicon near dioxide or "Si" near "O.sub.2" or "SiO") and ("Cu" or copper)) not (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 16:09
-	1612	257/758 not (257/758 and ("Cu" or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/16 17:47